

Amendments to the Specification

Please replace the abstract with the following amended paragraph:

A diode which eliminates [[the]] generation of local avalanche breakdown phenomenon when static surges in the backward direction are applied and ~~has excellent properties to withstand~~ withstands electrostatic breakdown ~~is to be provided~~. A P-type impurity diffused region of high concentration [[to be]] as an anode and an N-type impurity diffused region of high concentration [[to be]] as a cathode that surrounds the P-type impurity diffused region, are formed on the [[front]] surface of an N-type silicon well region. The surface of the N-type silicon well region on which the impurity diffused regions are formed is covered with an interlayer dielectric, and a metal interconnect layer is formed thereon, to spread to the border line of the N-type impurity diffused region and is electrically connected to the P-type impurity diffused region. Accordingly, a P-type inversion layer IP is uniformly formed in a separation area between the impurity diffused regions when static surges in the backward direction are applied, preventing [[a]] local avalanche breakdown ~~phenomenon~~.